United States Patent [19]

Wahlstrom

[11] Patent Number:

4,829,018

[45] Date of Patent:

May 9, 1989

[54] MULTILEVEL INTEGRATED CIRCUITS EMPLOYING FUSED OXIDE LAYERS

[76] Inventor: Sven E. Wahlstrom, 570 Jackson Dr., Palo Alto, Calif. 94303

[21] Appl. No.: 879,738

[22] Filed: Jun. 27, 1986

[56] References Cited

U.S. PATENT DOCUMENTS

3,508,980	4/1970	Jackson, Jr. et al.	148/DIG. 12
3,564,358	2/1971	Hahnlein	148/DIG. 164
3,959,045	5/1976	Antypas	148/DIG. 135
3,997,381	12/1976	Wanlass	156/657
4,009,057	2/1977	de Brebisson et al.	437/31
4,142,925	3/1979	King et al	148/DIG. 135
4,169,000	9/1979	Riseman	156/645
4,309,811	1/1982	Calhoun	
4,601,779	7/1986	Abernathey et al	148/1.5
4,612,083	9/1986	Yasumoto et al	148/DIG. 164
4,638,552	1/1987	Shimbo et al	148/DIG. 12
4,649,627	3/1987	Abernathey et al	148/DIG. 164

FOREIGN PATENT DOCUMENTS

0161740 11/1985 European Pat. Off. 148/DIG. 12

OTHER PUBLICATIONS

Ghandhi, VLSI Fabrication Principles, John Wiley and Sons, Inc., 1983.

Primary Examiner—Brian E. Hearn Assistant Examiner—M. Wilczewski

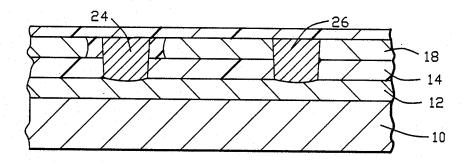
Attorney, Agent, or Firm—Flehr, Hohbach, Test,

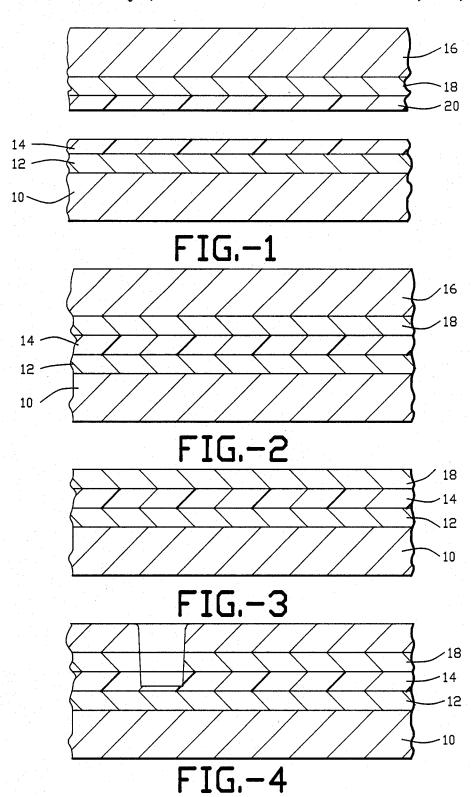
Albritton & Herbert

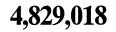
[57] ABSTRACT

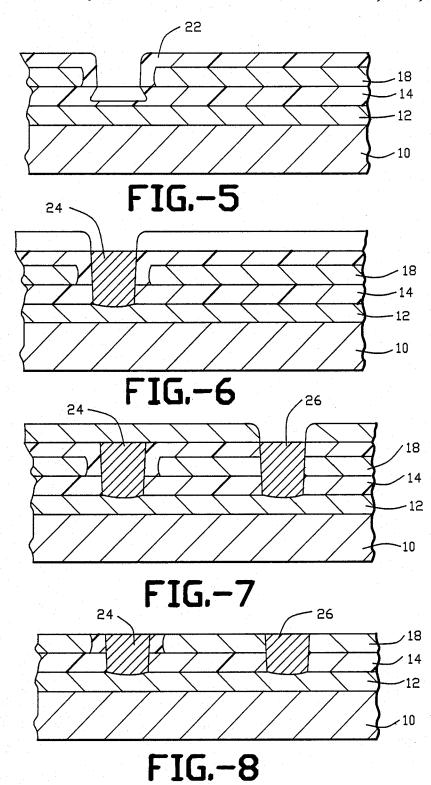
A multilevel semiconductor integrated circuit is fabricated by providing a plurality of substrates having an epitaxial layer on one surface and a silicon oxide layer on the surface of the epitaxial layer. The substrates are sequentially stacked with the silicon oxide layers in contact and fused together. One substrate is retained as a support, and other substrates are removed by etching after the fusion of the silicon oxide layers, thereby leaving only the stacked epitaxial layers separated by silicon oxide. The stacked structure facilitates the vertical fabrication of CMOS transistor pairs sharing a common gate electrode in an epitaxial layer between the two transistors. Electrical isolation between the epitaxial layers is provided by the fused silicon oxide or by removing the silicon oxide and some of the silicon thereby forming a void between adjacent epitaxial layers. Circuit devices in the plurality of epitaxial layers are readily interconnected by forming conductive vias between the epitaxial layers.

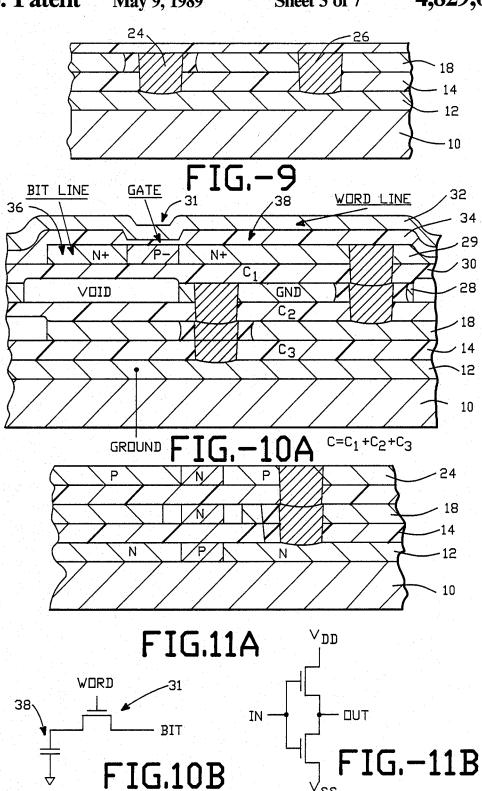
2 Claims, 7 Drawing Sheets

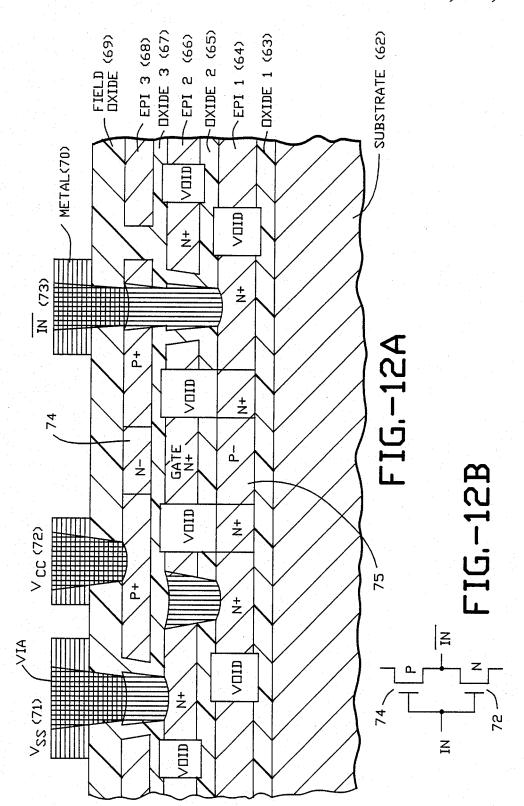












DOCKET A L A R M

Explore Litigation Insights



Docket Alarm provides insights to develop a more informed litigation strategy and the peace of mind of knowing you're on top of things.

Real-Time Litigation Alerts



Keep your litigation team up-to-date with **real-time** alerts and advanced team management tools built for the enterprise, all while greatly reducing PACER spend.

Our comprehensive service means we can handle Federal, State, and Administrative courts across the country.

Advanced Docket Research



With over 230 million records, Docket Alarm's cloud-native docket research platform finds what other services can't. Coverage includes Federal, State, plus PTAB, TTAB, ITC and NLRB decisions, all in one place.

Identify arguments that have been successful in the past with full text, pinpoint searching. Link to case law cited within any court document via Fastcase.

Analytics At Your Fingertips



Learn what happened the last time a particular judge, opposing counsel or company faced cases similar to yours.

Advanced out-of-the-box PTAB and TTAB analytics are always at your fingertips.

API

Docket Alarm offers a powerful API (application programming interface) to developers that want to integrate case filings into their apps.

LAW FIRMS

Build custom dashboards for your attorneys and clients with live data direct from the court.

Automate many repetitive legal tasks like conflict checks, document management, and marketing.

FINANCIAL INSTITUTIONS

Litigation and bankruptcy checks for companies and debtors.

E-DISCOVERY AND LEGAL VENDORS

Sync your system to PACER to automate legal marketing.

